

ABSTRACT

A semiconductor laser device, which is made from an AlGaInP-based material, comprising:

a first clad layer of a first conductivity type, an active layer and a second clad layer of a second conductivity type that are formed over a semiconductor substrate,

wherein a portion of said active layer in an area near a laser resonator end face has a peak wavelength in photoluminescence that is smaller than a peak wavelength in photoluminescence in a portion of said active layer in a laser resonator inner area, and the second clad layer of the second conductivity type located in the area near a laser resonator end face contains As atoms, and a manufacturing method thereof.